

by magnetic coils 803 and 803a, and Ar gas introduced from an introducing pipe 804 is activated as a high-density plasma by the electron cyclotron resonance.

IN THE CLAIMS:

Please cancel claim 4 and amend claims 5-9 as follows:

5. (Amended) A method of manufacturing a semiconductor device, said method comprising the steps of:

forming a wiring layer on a semiconductor substrate having an active region formed thereon;

forming a first insulating layer containing carbon on said wiring layer;

forming a second insulating layer comprising silicon, carbon and nitrogen on said first insulating layer;

adding boron to said second insulating layer;

selectively etching said second insulating layer until the surface of said first insulating layer is partially exposed;

selectively etching said first insulating layer with plasma, using said selectively-etched second insulating layer as a mask pattern; and

forming a new wiring layer on said second insulating layer after selectively etching said first insulating layer.

6. (Amended) The method of manufacturing a semiconductor device as set forth in claim 5, wherein said step of selectively etching said second insulating layer is carried out with the plasma of the gas of a compound containing carbon and fluorine.

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7. (Amended) The method of manufacturing a semiconductor device as set forth in claim 5, wherein said step of selectively etching said second insulating layer is carried out with the plasma of the gas of a compound containing carbon and hydrogen.

8. (Amended) The method of manufacturing a semiconductor device as set forth in claim 5, wherein said step of selectively etching said second insulating layer is carried out with the plasma of an oxygen-containing gas.

9. (Amended) The method of manufacturing a semiconductor device as set forth in claim 5, wherein said step of selectively etching said second insulating layer is carried out with the plasma of a hydrogen-containing gas.

REMARKS

In the last Office Action, the Examiner rejected claims 4 and 8 under 35 U.S.C. § 103(a) as being unpatentable over Zhao et al. (U.S. Patent No. 6,100,184) ("Zhao") in view of Moore et al. (U.S. Patent No. 6,251,802) ("Moore"), rejected claim 5 under 35 U.S.C. § 103(a) as being unpatentable over Zhao in view of Moore and further in view of Fraser et al. (U.S. Patent No. 4,244,799) ("Fraser"), rejected claims 6 and 7 under 35 U.S.C. § 103(a) as being unpatentable over Zhao in view of Moore and further in view of Wolf et al. ("Wolf"), and rejected claim 9 under 35 U.S.C. § 103(a) as being unpatentable over Zhao in view of Moore and further in view of Chen et al. (U.S. Patent No. 6,211,061) ("Chen").

By this Amendment, Applicant has cancelled claim 4, without prejudice or disclaimer, and has rewritten claim 5 in independent form. Applicant has also amended claims 6-9 to depend from independent claim 5. Applicant has made additional changes to the specification and the claims solely to correct inadvertent and

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